Sialon-based oxynitride phosphor, process for its production, and use thereof

Patent number: EP1445295
Publication date: 2004-08-11
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Classification:
- international: *C09K11/08; C09K11/77; H01L33/00;* C09K11/08; C09K11/77; H01L33/00; (IPC1-7): C09K11/08; C04B35/00; C09K11/77; H01L33/00; H05B33/14
- european: C09K11/08J; C09K11/77D; C09K11/77M6; C09K11/77N6; C09K11/77P6; C09K11/77S6
Application number: EP20040002508 20040205
Priority number(s): JP20030029274 20030206; JP20030029277 20030206

Also published as:
US2004155225 (A1)

Cited documents:
EP1278250
EP1264873
XP001151981
XP004215129

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Abstract of **EP1445295**

An alpha -sialon-based oxynitride phosphor characterized in that the content of alpha -sialon represented by the general formula: MxSi12-(m+n)Al(m+n)OnN16-n:Lny (wherein M is at least one metal selected from among Li, Ca, Mg, Y or lanthanide metals excluding La and Ce, Ln is at least one lanthanide metal selected from among Ce, Pr and La or at least one lanthanide metal selected from among Eu, Dy, Er, Tb and Yb, 0.3<=x+y<1.5, 0<y<0.7, 0.3<=m<4.5, 0<n<2.25, and m = ax + by, where a is the valence of the metal M and b is the valence of the lanthanide metal Ln), wherein all or a portion of the metal M dissolved in the alpha -sialon is replaced with the lanthanide metal Ln as the luminescence center, is 75 wt% or greater when the lanthanide metal Ln is at least one lanthanide metal selected from among Ce, Pr and La and 90 wt% or greater when the lanthanide metal Ln is at least one lanthanide metal selected from among Eu, Dy, Er, Tb and Yb, and in that the content of metal impurities other than the metal M, lanthanide metal Ln, silicon, IIIA elements (aluminum, gallium), oxygen and nitrogen, is no greater than 0.01 wt%.